

On page 12, line 22, change "bonds" to --bond connections--.
On page 12, line 28, change "bond" to --bond connection--.
On page 13, line 9, after "embodiment" insert --of the present invention-- and delete "essentially".

On page 13, replace line 23 with --Binary coding of the resistance values may be used, making it--.

On page 13, line 29, change "must be" to --are--.

On page 14, line 13, change "step size" to --increment, or step size,--.

On page 15, line 21, after "array" insert --of the present invention--.

On page 15, line 25, change "bonds" to --bond connections--.

On page 16, line 7, after "embodiment" insert --of the present invention--.

On page 16, line 12, change "preferably" to --such as--.

On page 16, line 19, after "embodiment" insert --of the present invention--.

On page 16, line 22, change "bonds" to --bond connections--.

On page 16, line 25 after "embodiment" insert --of the present invention--.

On page 16, line 30, after "embodiment" insert --of the present invention--.

On page 17, line 4, change "bonds" to --bond connections--.

On page 17, line 6, after "embodiment" insert --of the present invention--.

On page 17, line 20, after "embodiment" insert --of the present invention--.

On page 18, line 4, after "embodiments" insert --of the present invention--.

Delete all lines on page 19.

On page 20, line 1, change "Patent Claims" to --WHAT IS CLAIMED IS:--.

IN THE CLAIMS

Please cancel without prejudice claims 1-17 and add new claims 18-36 as follows:

--18. (new) A method for the wavelength tuning of an optoelectronic component array, the optoelectronic component array including at least two optoelectronic components, the method comprising:

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comparing a respective measured wavelength with a respective desired characteristic wavelength so as to determine a respective wavelength deviation for each of the at least two optoelectronic components; and

selectively changing a respective resistance value of a respective resistor arrangement connected between each of the at least two optoelectronic components and a respective resistance heater associated with each of the at least two optoelectronic components so as to achieve a respective thermal change of the respective resistance heater for setting the respective desired characteristic wavelength of each of the at least two optoelectronic components.

19. (new) The method as recited in claim 18 wherein the selectively changing is performed using circuitry.

20. (new) The method as recited in claim 18 wherein the selectively changing is performed by changing a respective material of the respective resistor arrangement.

21. (new) The method as recited in claim 20 wherein the changing a respective material of the respective resistor arrangement is performed by removing or applying the respective material.

22. (new) The method as recited in claim 18 wherein the selectively changing is performed using laser ablation.

23. (new) The method as recited in claim 18 wherein the selectively changing is performed using heat treatment.

24. (new) The method as recited in claim 18 wherein the selectively changing is performed using at least one of a chemical and an electrochemical treatment.

25. (new) The method as recited in claim 18 wherein the selectively changing is performed using at least one of particle implantation, electromagnetic radiation and particle radiation.

26. (new) The method as recited in claim 18 wherein the selectively changing is performed using an electrical signal.

27. (new) The method as recited in claim 18 wherein the method is performed at regular intervals.

28. (new) A device for the wavelength tuning of an optoelectronic component array having at least two optoelectronic components, the device comprising:

a respective at least one resistance heater associated with each of the at least two optoelectronic components for setting a respective characteristic wavelength of the respective optoelectronic component;

a common voltage or current source; and

a respective resistor arrangement connected between each respective at least one resistance heater and the common voltage or current source, a respective total resistance of each respective resistor arrangement being variable.

29. (new) The device as recited in claim 28 wherein each respective resistor arrangement includes respective individual resistors disposed in a respective resistor array.

30. (new) The device as recited in claim 28 wherein respective resistors of each respective resistor arrangement are connected between a respective contact fields disposed in rows, the respective resistors being arranged in a fixed order with regard to their respective resistance values, a respective total resistance of each respective resistor arrangement being achieved using the respective contact fields.

31. (new) The device as recited in claim 30 wherein the respective total resistance of each respective resistor arrangement is achieved using bond connections.